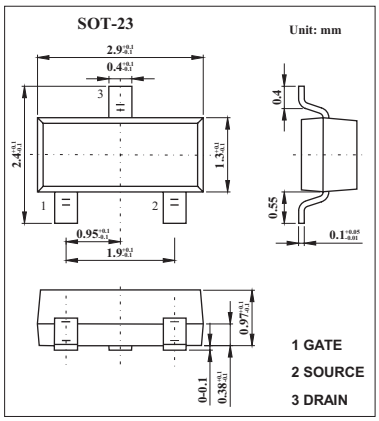
MOS Fied Effect Transistor

2SJ209



Features

- Directly driven by Ics having a 5V poer supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the biasresistor.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage VGS=0	VDSS	-100	V
Gate to source voltage VDS=0	VGSS	±16	V
Drain current (DC)	ID	±100	m A
Drain current(pulse) *	ID	±200	m A
Power dissipation	PD	200	m W
Channel temperature	Tch	150	℃
Storage temperature	Tstg	-55 to +150	℃

* PW ⩽ 10 ms; d ⩽ 50%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	IDSS	VDS=-100V,VGS=0			-10	μA
Gate leakage current	IGSS	VGS=±16V,VDS=0			±10	μA
Gate cut-off voltage	VGS(off)	VDS=-5.0V,ID=-1μA	-1.5	-2.0	-2.5	V
Forward transfer admittance	|Yfs|	VDS=-5.0V,ID=-10mA	15	22		ms
Drain to source on-state resistance	RDS(on)	VGS=-4.0V,ID=-10mA		60	100	Ω
		VGS=-10V,ID=-10mA		37	60	Ω
Input capacitance	Ciss	VDS=-5.0V,VGS=0,f=1MHZ		17		pF
Output capacitance	Coss			9		pF
Reverse transfer capacitance	Crss			1		pF
Turn-on delay time	td(on)	VGS(on)=-4V,RG=10Ω,VDD=-5V,ID=-10mA RL=500Ω		45		ns
Rise time	tr			75		ns
Turn-off delay time	td(off)			25		ns
Fall time	tf			80		ns

Marking

Marking	H17